## SQD50P04-09L



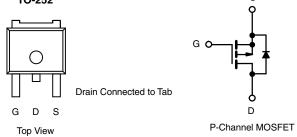
**Vishay Siliconix** 

# Automotive P-Channel 40 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY					
V <sub>DS</sub> (V)	- 40				
$R_{DS(on)} (\Omega)$ at $V_{GS} = -10 \text{ V}$	0.0094				
$R_{DS(on)}(\Omega)$ at $V_{GS} = -4.5 V$	0.0190				
I <sub>D</sub> (A)	- 50				
Configuration	Single				

S

#### TO-252



#### FEATURES

- Halogen-free According to IEC 61249-2-21
  Definition
- TrenchFET<sup>®</sup> Power MOSFET
- Package with Low Thermal Resistance
- 100 % R<sub>g</sub> and UIS Tested
- Compliant to RoHS Directive 2002/95/EC
- AEC-Q101 Qualified<sup>d</sup>



ORDERING INFORMATION	
Package	TO-252
Lead (Pb)-free and Halogen-free	SQD50P04-09L-GE3

<b>ABSOLUTE MAXIMUM RATINGS</b> ( $T_C = 25 \degree C$ , unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V <sub>DS</sub>	- 40	V	
Gate-Source Voltage		V <sub>GS</sub>	± 20	V	
Continuous Drain Current <sup>a</sup>	T <sub>C</sub> = 25 °C	1	- 50		
Continuous Drain Current <sup>a</sup>	T <sub>C</sub> = 125 °C	Ι <sub>D</sub>	- 50		
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	- 50	A	
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	- 200		
Single Pulse Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	- 50		
Single Pulse Avalanche Energy	L = 0.1 MH	E <sub>AS</sub>	125	mJ	
Maximum Power Dissipation <sup>b</sup>	T <sub>C</sub> = 25 °C	D	136	W	
Maximum Fower Dissipation	T <sub>C</sub> = 125 °C	P <sub>D</sub>	45	vv	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 175	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount <sup>c</sup>	R <sub>thJA</sub>	50	°C/W	
Junction-to-Case (Drain)		R <sub>thJC</sub>	1.1	0/10	

#### Notes

- a. Package limited.
- b. Pulse test; pulse width  $\leq 300~\mu\text{s},~\text{duty}~\text{cycle} \leq 2~\%.$
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.

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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static					•	•		
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, \text{ I}_{D} = -250 \mu\text{A}$		- 40	-	-	v	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = - 250 μA		-	- 2.5		
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$V_{DS} = 0 V, V_{GS} = \pm 20 V$		-	± 100	nA	
		$V_{GS} = 0 V$	V <sub>DS</sub> = - 40 V	-	-	- 1		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{GS} = 0 V$	$V_{DS}$ = - 40 V, T <sub>J</sub> = 125 °C	-	-	- 50	μA	
		$V_{GS} = 0 V$	$V_{DS}$ = - 40 V, T <sub>J</sub> = 175 °C	-	-	- 150		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = - 10 V	$V_{DS} \le -5 V$	- 50	-	-	Α	
		V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 17 A	-	0.0076	0.0094	Ω	
Ducia Course On Otata Desistance?		V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 50 A, T <sub>J</sub> = 125 °C	-	-	0.014		
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 50 A, T <sub>J</sub> = 175 °C	-	-	0.017		
		V <sub>GS</sub> = - 4.5 V	I <sub>D</sub> = - 14 A	-	0.012	0.019		
Forward Transconductanceb	g <sub>fs</sub>	V <sub>DS</sub> =	V <sub>DS</sub> = - 15 V, I <sub>D</sub> = - 17 A		46	-	S	
Dynamic <sup>b</sup>	·				•			
Input Capacitance	C <sub>iss</sub>			-	5339	6675		
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	0 V V <sub>DS</sub> = - 20 V, f = 1 MHz	-	852	1065	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>			-	681	855		
Total Gate Charge <sup>c</sup>	Qg			-	103	155		
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = - 10 V	10 V V <sub>DS</sub> = - 20 V, I <sub>D</sub> = - 50 A		24	-	nC	
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			-	16	-		
Gate Resistance	Rg	f = 1 MHz		1.4	2.8	4.2	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			-	13	20		
Rise Time <sup>c</sup>	t <sub>r</sub>	$\label{eq:VDD} \begin{array}{l} V_{\text{DD}} = \text{-} \ 20 \ \text{V}, \ R_{\text{L}} = 0.4 \ \Omega \\ I_{\text{D}} \cong \text{-} \ 50 \ \text{A}, \ V_{\text{GEN}} = \text{-} \ 10 \ \text{V}, \ R_{\text{g}} = 1 \ \Omega \end{array}$		-	15	23	- ns	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			-	61	92		
Fall Time <sup>c</sup>	t <sub>f</sub>			-	19	29		
Source-Drain Diode Ratings and Char	acteristics <sup>b</sup>	•						
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	- 200	Α	
		I <sub>F</sub> = - 50 A, V <sub>GS</sub> = 0 V			1			

Notes

a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$ 

b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

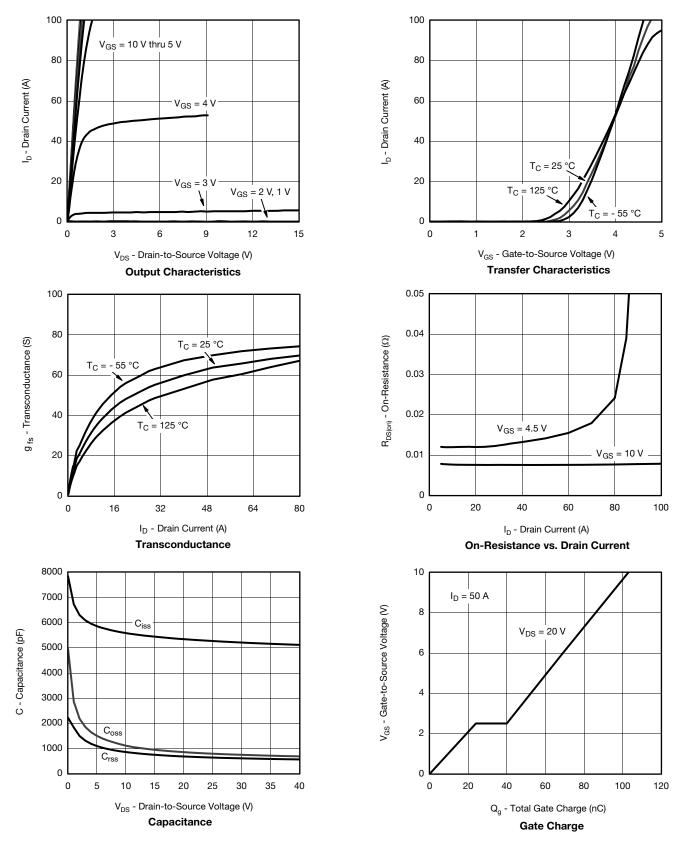
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



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## **TYPICAL CHARACTERISTICS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



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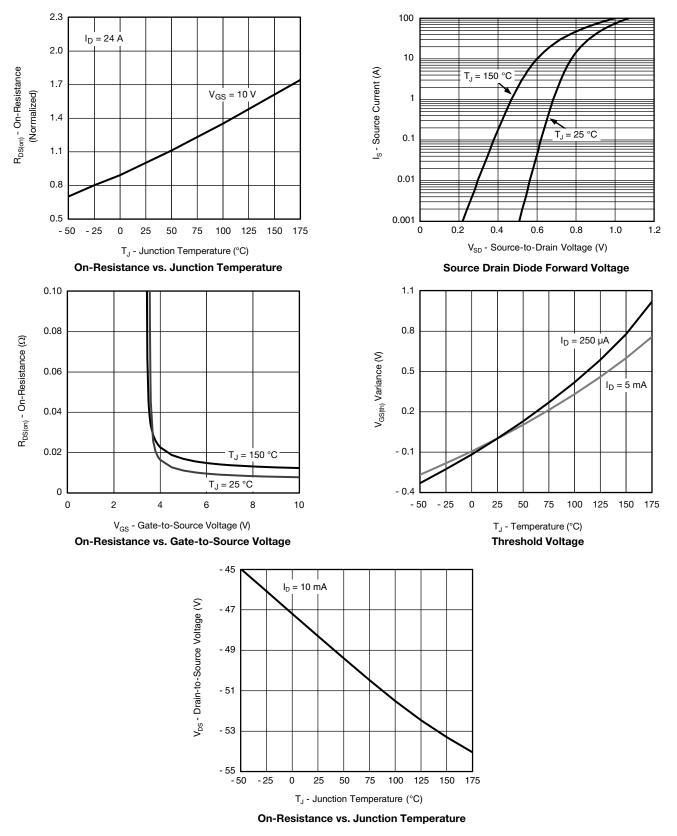
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## **TYPICAL CHARACTERISTICS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



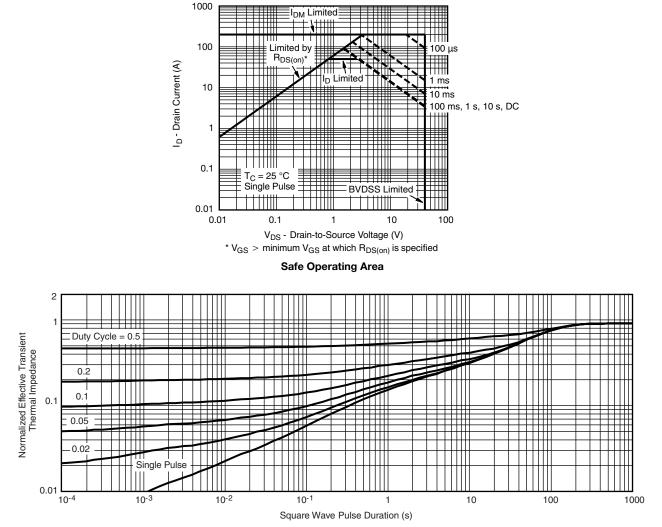
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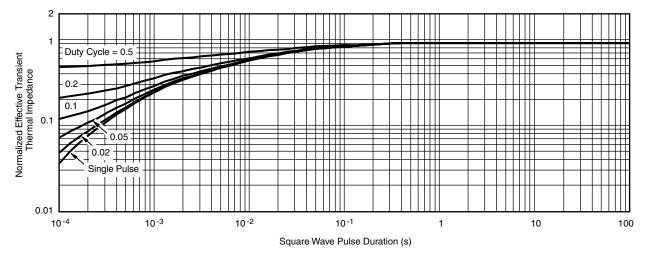
#### **THERMAL RATINGS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



## **THERMAL RATINGS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

The characteristics shown in the two graphs

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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# C2 т gage plane height (0.5 mm)

-C

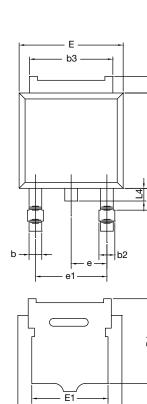
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**TO-252AA** Case Outline

	MILLIN	<b>IETERS</b>	INCHES		
DIM.	MIN.	MAX.	MIN.	MAX.	
А	2.18	2.38	0.086	0.094	
A1	-	0.127	-	0.005	
b	0.64	0.88	0.025	0.035	
b2	0.76	1.14	0.030	0.045	
b3	4.95	5.46	0.195	0.215	
С	0.46	0.61	0.018	0.024	
C2	0.46	0.89	0.018	0.035	
D	5.97	6.22	0.235	0.245	
D1	4.10	-	0.161	-	
Е	6.35	6.73	0.250	0.265	
E1	4.32	-	0.170	-	
Н	9.40	10.41	0.370	0.410	
е	2.28	BSC	0.090	0.090 BSC	
e1	4.56 BSC		0.180 BSC		
L	1.40	1.78	0.055	0.070	
L3	0.89	1.27	0.035	0.050	
L4	-	1.02	-	0.040	
L5	1.01	1.52	0.040	0.060	
ECN: T13-0592-Rev. A, 02-Sep-13 DWG: 6019					

Note

• Dimension L3 is for reference only.





#### **RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)**



Recommended Minimum Pads Dimensions in Inches/(mm)

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